

isc Silicon PNP Darlington Power Transistor

2SB1624

DESCRIPTION

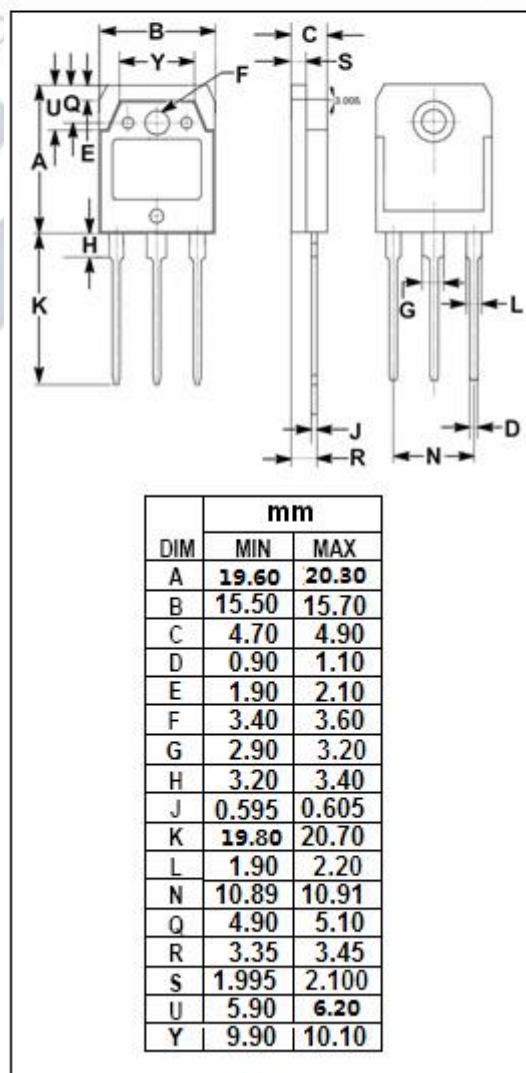
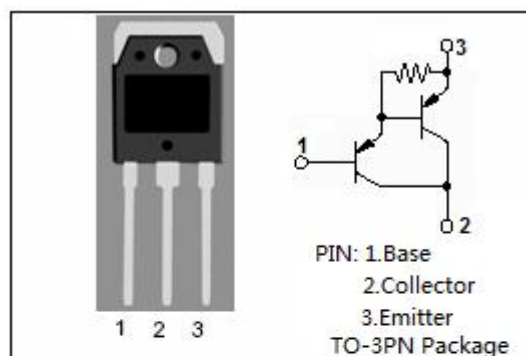
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -110V(\text{Min})$
- Low-Collector Saturation Voltage-
: $V_{CE(sat)} = -2.5V(\text{Max.})@I_C = -5A$
- Complement to Type 2SD2493
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio, series regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-110	V
V_{CEO}	Collector-Emitter Voltage	-110	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6	A
I_B	Base Current- Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Darlington Power Transistor**2SB1624****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-110			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -5\text{mA}$			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -5\text{mA}$			-3.0	V
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-100	μA
I_{CBO}	Collector Cutoff Current	$V_{CB} = -110\text{V}; I_E = 0$			-100	μA
h_{FE}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	5000		30000	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -12\text{V}$		100		MHz

◆ h_{FE} Classifications

O	P	Y
5000-12000	6500-20000	15000-30000